Synthesis, Optical Properties, and Photochemical Activity of Zinc-Indium-Sulfide Nanoplates

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Figure S1: TEM images of ZIS nanoplates



Figure S2: Tauc's plot of absorbance squared versus energy. The linear relationship signifies a direct band gap. The extrapolation to the energy axis give the bandgap. There is a significant contribution from below gap absorption likely resulting from defect states within the forbidden gap.



ZIS0

ZIS50











Z13.



Figure S3: Global fits to TR PL data using EQ1 for samples ZISO, ZIS5O, ZIS15O, and ZIS25O. Residuals have been normalised to the experimental data as to more faithfully reflect inaccuracies. Dynamics were convolved with appropriate TR PL system temporal response functions. Some secondary excitations arising from leaked pulses in the acousto-optical modulator can be seen.



Figure S4: Temporal integrals of the TR PL global fit components. In each case, the time-integrated emission is dominated by long lifetime component ($^{\tau_2}$) despite its low relative amplitude. The CW experimental data are also plotted for comparison.